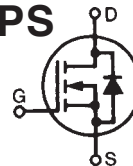


# PolarHV™ Power MOSFET

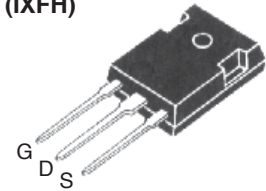
N-Channel Enhancement Mode  
Fast Recovery Diode  
Avalanche Rated

**IXFH 26N60P**  
**IXFQ 26N60P**  
**IXFT 26N60P**  
**IXFV 26N60P**  
**IXFV 26N60PS**

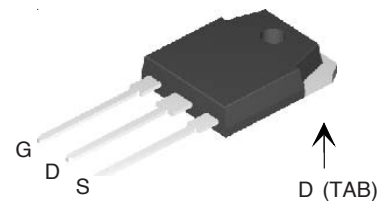
$V_{DSS} = 600 \text{ V}$   
 $I_{D25} = 26 \text{ A}$   
 $R_{DS(on)} \leq 270 \text{ m}\Omega$   
 $t_{rr} \leq 200 \text{ ns}$



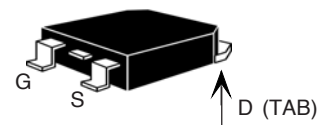
TO-247 (IXFH)



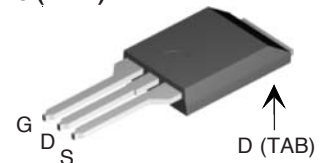
TO-3P (IXFQ)



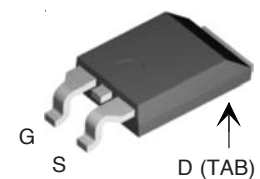
TO-268 (IXFT)



PLUS220 (IXFV)



PLUS220SMD (IXFV\_S)



G = Gate  
S = Source  
D = Drain  
TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	600	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	26	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	65	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	26	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	40	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.2	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 5 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	460	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s Plastic body	300 250	$^\circ\text{C}$ $^\circ\text{C}$
$M_d$	Mounting torque (TO-3P&TO-247)	1.13/10	Nm/lb.in.
$F_c$	Mounting force (PLUS220)	11..65/2.5..15	N/lb
Weight	TO-3P	5.5	g
	TO-248	6.0	g
	TO-268	5.0	g
	PLUS220 & PLUS220SMD	4.0	g

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$
				250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2 \%$			270 $\text{m}\Omega$

### Features

- Fast Recovery diode
- Unclamped Inductive Switching (UIS) rated
- International standard packages
- Low package inductance
- easy to drive and to protect

### Advantages

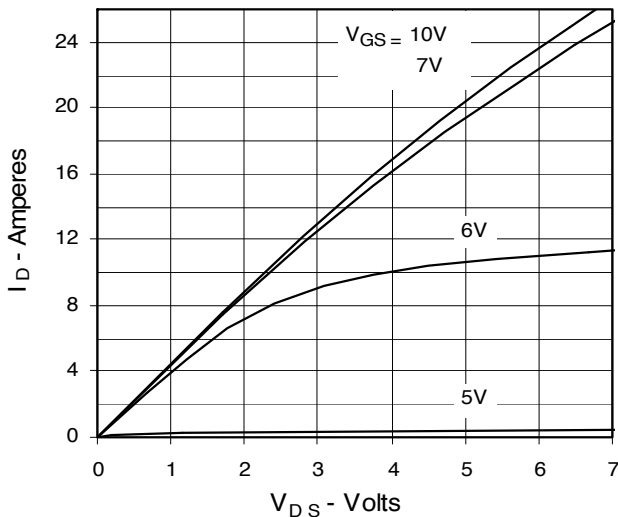
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 0.5 I <sub>D25</sub> , pulse test	16	26	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		4150	pF
<b>C<sub>oss</sub></b>			400	pF
<b>C<sub>rss</sub></b>			27	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 I <sub>D25</sub> R <sub>G</sub> = 5 Ω (External)		25	ns
<b>t<sub>r</sub></b>			27	ns
<b>t<sub>d(off)</sub></b>			75	ns
<b>t<sub>f</sub></b>			21	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub>		72	nC
<b>Q<sub>gs</sub></b>			27	nC
<b>Q<sub>gd</sub></b>			24	nC
<b>R<sub>thJC</sub></b>	TO-3P, PLUS220 & TO-247			0.27 K/W
<b>R<sub>thCK</sub></b>			0.21	K/W

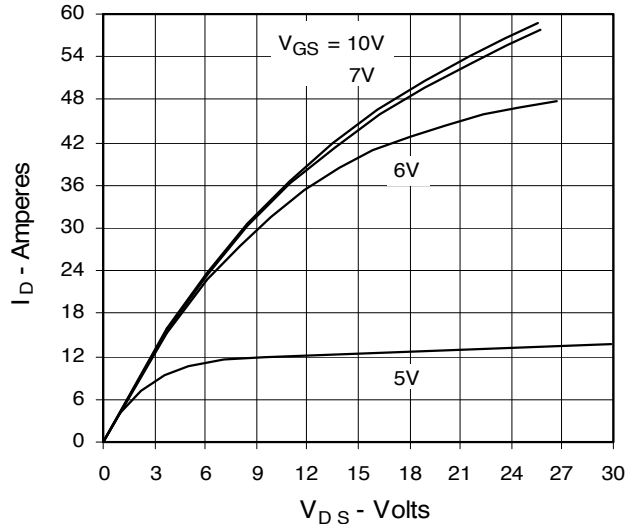
Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			26 A
<b>I<sub>SM</sub></b>	Repetitive			78 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, pulse test			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 25A, -di/dt = 100 A/μs	150	250	ns
<b>I<sub>RM</sub></b>	V <sub>R</sub> = 100V; V <sub>GS</sub> = 0 V	7		A
<b>Q<sub>RM</sub></b>		0.7		μC

**Characteristic Curves**

**Fig. 1. Output Characteristics @ 25°C**



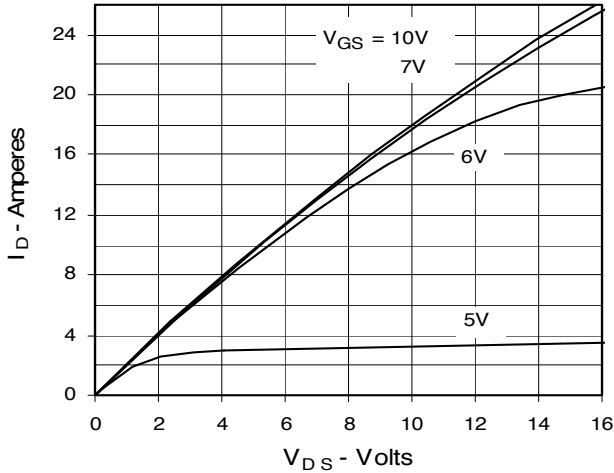
**Fig. 2. Extended Output Characteristics @ 25°C**



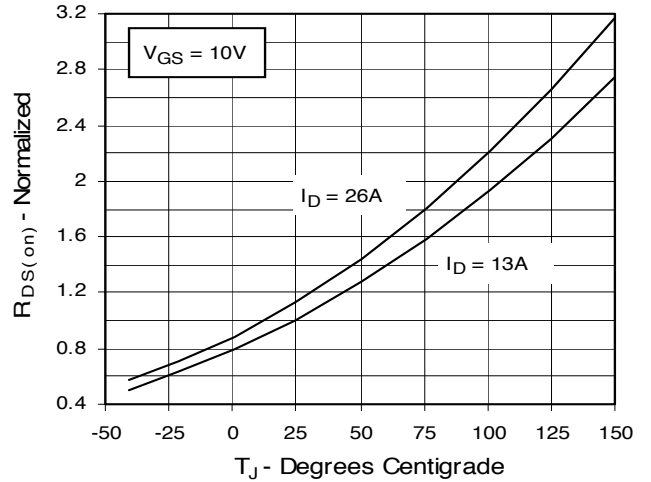
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

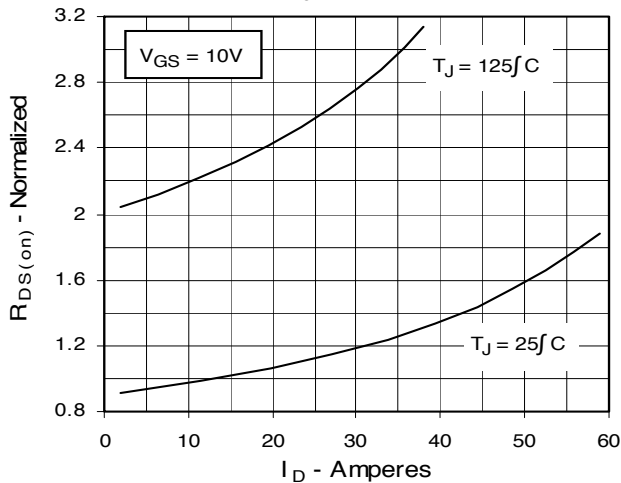
**Fig. 3. Output Characteristics @ 125°C**



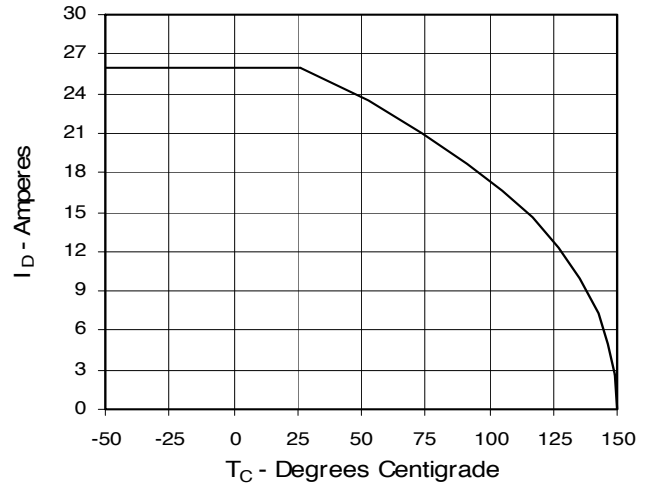
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



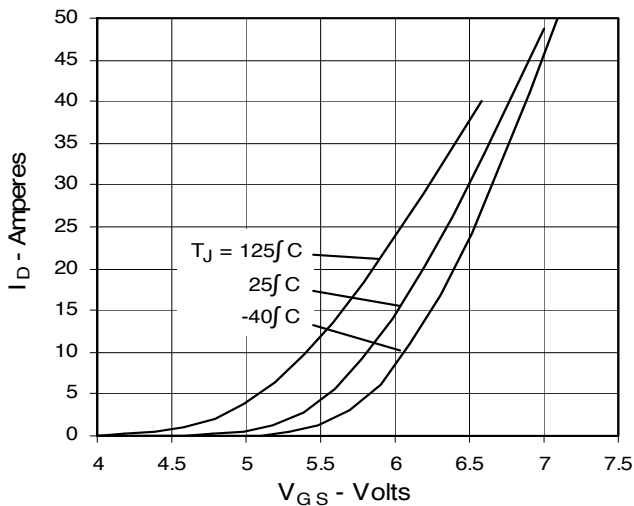
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



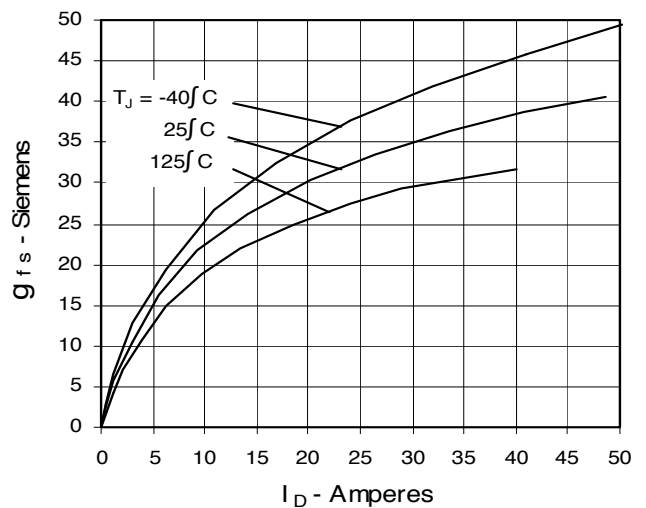
**Fig. 6. Drain Current vs. Case Temperature**



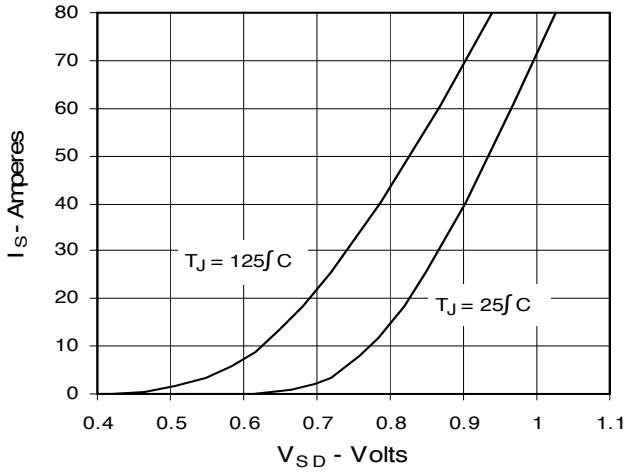
**Fig. 7. Input Admittance**



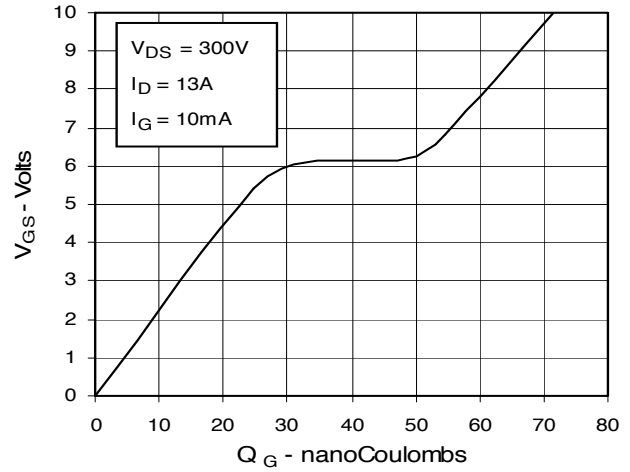
**Fig. 8. Transconductance**



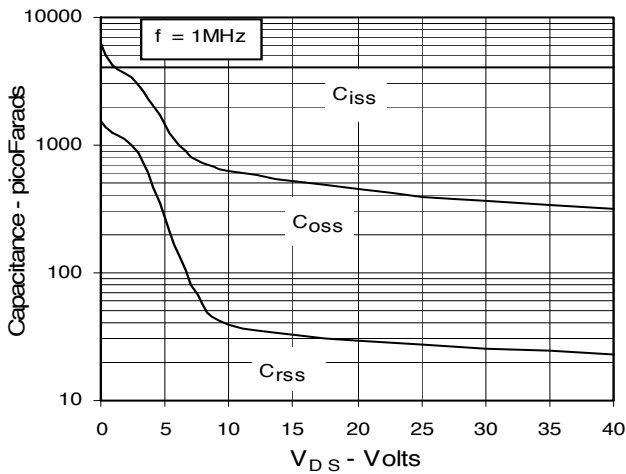
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



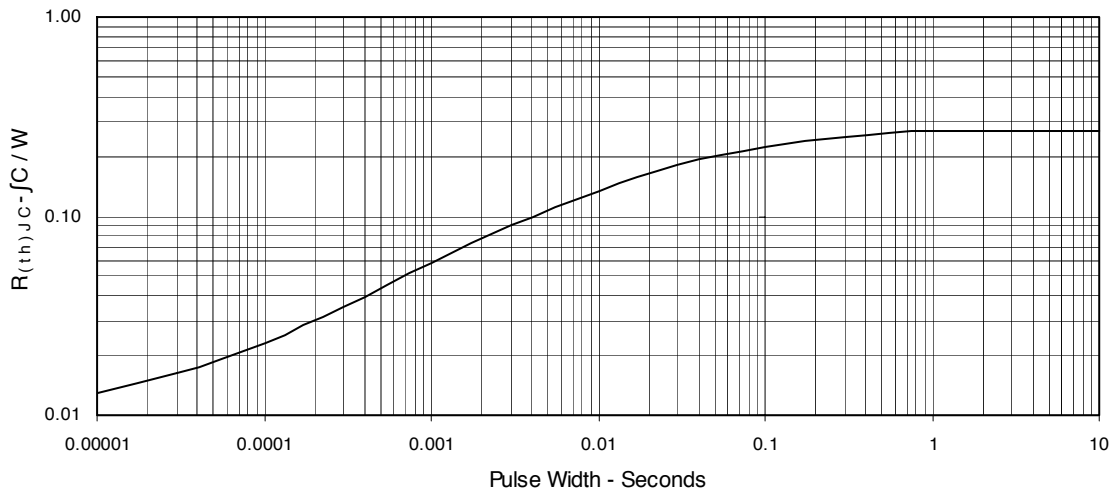
**Fig. 10. Gate Charge**



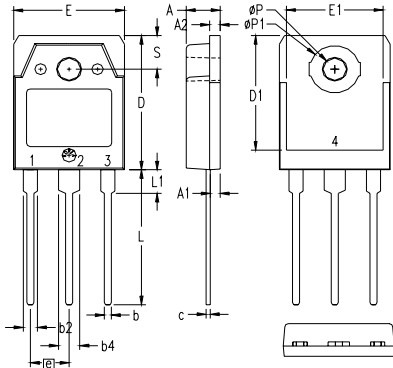
**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



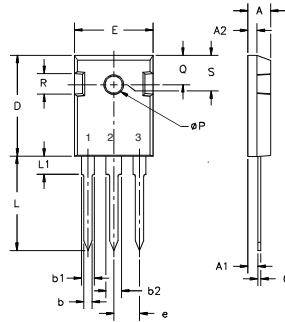
### TO-3P (IXFQ) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
phi P	.126	.134	3.20	3.40
phi P1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

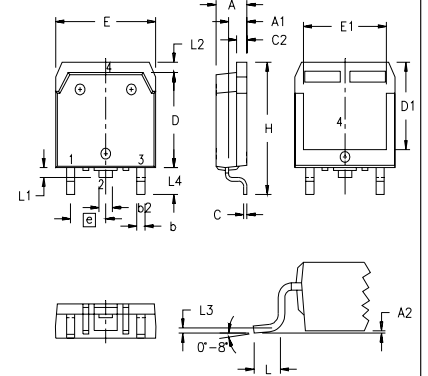
All metal area are tin plated.

### TO-247 AD (IXFH) Outline



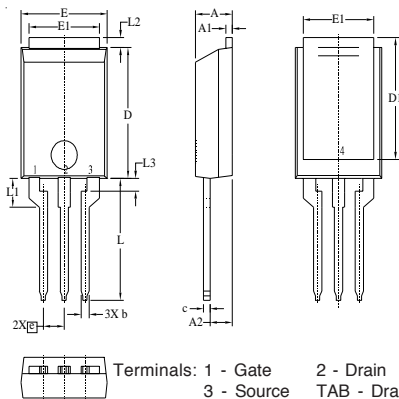
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A1	2.2	2.54	.087	.102
A2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b1	1.65	2.13	.065	.084
b2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1	4.50		.177	
phi P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

### TO-268 (IXFT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

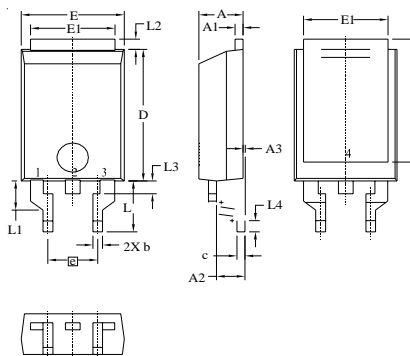
### PLUS220 (IXFV) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source TAB - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100 BSC		2.54 BSC	
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50

### PLUS220SMD (IXFV\_S)



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
A3	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.200BSC		5.08 BSC	
L	.209	.228	5.30	5.80
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50
L4	.039	.059	1.00	1.50

Terminals:  
1 - Gate  
2 - Drain  
3 - Source  
4 (TAB) - Drain